Metrics	*Today*		*Program Goal*
$T_{operation}$ (°C)	RT to 300 °C		200
BV (kV)	10		15
R_{on} (unipolar)* (_-cm^2)	0.13		0.3
V_t (V) (PIN / IGBT)	3.8 (PIN)		≤ 4.5 / ≤ 6
V_{th} (V) (MOSFET / IGBT)	N/A		5±0.2 / 5±0.2
I_{ON} (A) (PIN / MOSFET / IGBT)	7 (PIN)/0.1 (MOSFET)		≥ 45 / ≥18 / ≥ 25
Switch freq (kHz)	on wafer/0.5 µs PIN		20
Die Yield (%)	N/A		≥ 50
Half Bridge Modules I_{ON} (A)	N/A		110 A, 15 kV